

G.E. Zardas, P.H. Yannakopoulos, Chrys. I. Symeonides and P.C. Euthymiou

Persistent photoconductivity and energy gap of GaAs and InP

ABSTRACT. In this work we have analysed some very interesting results obtained for SI-GaAs samples, using photoconductivity measurements versus photon energy in the temperature range from 250 to 350 K. From the shape of the peaks measured, based on our analysis we can conclude that there is more than one interband transition involved. For these peaks we have calculated the energies. The relation of the interband transition energy versus temperature is linear.

Nanotechnology Perceptions **4** (2008) 35–42

Nonsubscribers: [purchase individual article](#)